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November 2013

FDD5N50NZF

N-Channel UniFETTM FRFET[®] MOSFET 500 V, 3.7 A, 1.75 Ω

Features

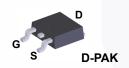
- $R_{DS(on)}$ = 1.47 Ω (Typ.) @ V_{GS} = 10 V, I_D = 1.85 A
- Low Gate Charge (Typ. 9 nC)
- Low C_{rss} (Typ. 4 pF)
- · 100% Avalanche Tested
- · Improved dv/dt Capability
- · ESD Imoroved Capability
- · RoHS Compliant

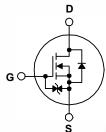
Applications

- LCD/LED/PDP TV
- · Lighting
- · Uninterruptible Power Supply

Description

UniFETTM II MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on advanced planar stripe and DMOS technology. This advanced MOSFET family has the smallest on-state resistance among the planar MOSFET, and also provides superior switching performance and higher avalanche energy strength. In addition, internal gate-source ESD diode allows UniFET II MOSFET to withstand over 2kV HBM surge stress. The body diode's reverse recovery performance of UniFET II FRFET® MOSFET has been enhanced by lifetime control. Its t_{rr} is less than 100nsec and the reverse dv/dt immunity is 15V/ns while normal planar MOSFETs have over 200nsec and 4.5V/nsec respectively. Therefore, it can remove additional component and improve system reliability in certain applications in which the performance of MOSFET's body diode is significant. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter		FDD5N50NZFTM	Unit
V _{DSS}	Drain to Source Voltage			500	V
V _{GSS}	Gate to Source Voltage			±25	V
	Drain Current	- Continuous (T _C = 25°C)		3.7	А
'D	Diam Current	- Continuous (T _C = 100°C)		2.2	7 ^
I _{DM}	Drain Current	- Pulsed	(Note 1)	14	Α
E _{AS}	Single Pulsed Avalanche E	Energy	(Note 2)	165	mJ
I _{AR}	Avalanche Current		(Note 1)	3.3	Α
E _{AR}	Repetitive Avalanche Ener	gy	(Note 1)	6.25	mJ
dv/dt	Peak Diode Recovery dv/c	It	(Note 3)	20	V/ns
D	Dower Dissipation	(T _C = 25°C)		62.5	W
P_{D}	Power Dissipation	- Derate Above 25°C		0.5	W/°C
T _J , T _{STG}	Operating and Storage Te	mperature Range		-55 to +150	οС
T _L	Maximum Lead Temperatu	re for Soldering, 1/8" from Case for 5	Seconds	300	°C

Thermal Characteristics

Symbol	Parameter FDD5N50NZFTM		Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max.		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max. 62.5		C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDD5N50NZFTM	FDD5N50NZF	DPAK	Tape and Reel	330 mm	16 mm	2500 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_C = 25^{\circ}C$	500	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C	-	0.5	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 500 V, V _{GS} = 0 V	-	-	10	^
DSS	Zero Gate voltage Drain Current	$V_{DS} = 400 \text{ V}, V_{GS} = 0 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	100	μА
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 25 \text{ V}, V_{DS} = 0 \text{ V}$	-	-	±10	μΑ

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 1.85 A	-	1.47	1.75	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 20 V, I _D = 1.85 A	-	4.2	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V - 25 V V - 0 V		-	365	485	pF
C _{oss}	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1 MHz		-	50	65	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 WILLS		-\	4	8	pF
Q _{g(tot)}	Total Gate Charge at 10V	V _{DS} = 400 V I _D = 3.7 A,		- \	9	12	nC
Q_{gs}	Gate to Source Gate Charge	V _{GS} = 10 V		- \	2	-	nC
Q _{qd}	Gate to Drain "Miller" Charge		(Note 4)	-	4	-	nC

Switching Characteristics

t _{d(on)}	Turn-On Delay Time			-	12	35	ns
t _r	Turn-On Rise Time	$V_{DD} = 250 \text{ V}, I_D = 3.7 \text{ A},$		-	19	50	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_G = 25 Ω		- /	31	70	ns
t _f	Turn-Off Fall Time		(Note 4)	-	22	55	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode	Maximum Continuous Drain to Source Diode Forward Current		-	3.7	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	14	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 3.7 A	-	-	1.5	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 3.7 A,	-	87	-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100 A/\mu s$	-	0.15	-	μС

Notes

- 1. Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L = 23 mH, I_{AS} = 3.7 A, V_{DD} = 50 V, R_G = 25 Ω , starting T_J = 25°C.
- 3. I $_{SD} \leq$ 3.7 A, di/dt \leq 200 A/µs, V $_{DD} \leq$ BV $_{DSS},$ starting T $_{J}$ = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

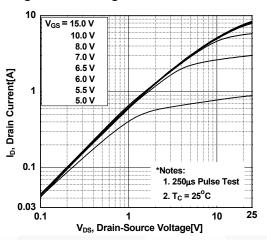


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

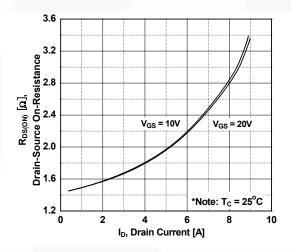


Figure 5. Capacitance Characteristics

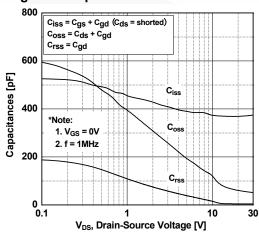


Figure 2. Transfer Characteristics

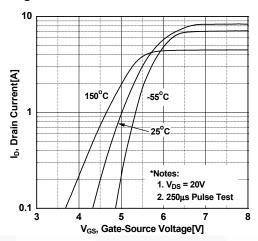


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

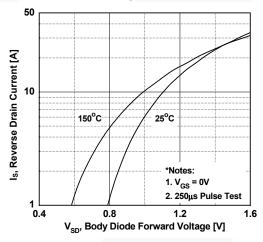
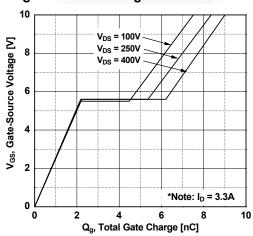


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

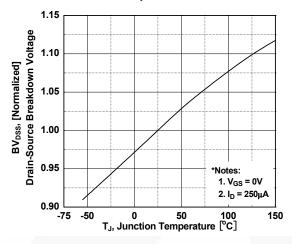


Figure 8. Maximum Safe Operating Area

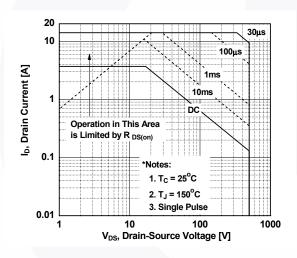


Figure 9. Maximum Drain Current vs. Case Temperature

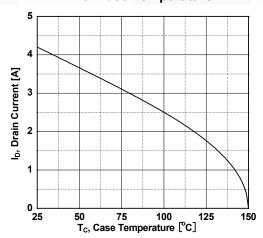
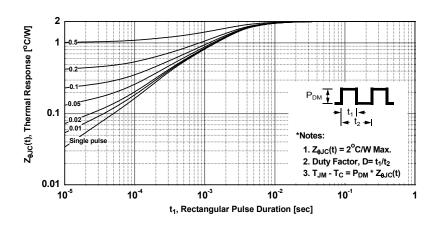


Figure 10. Transient Thermal Response Curve



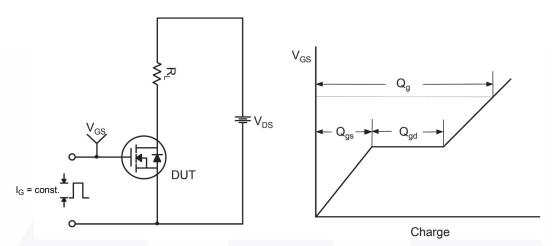


Figure 11. Gate Charge Test Circuit & Waveform

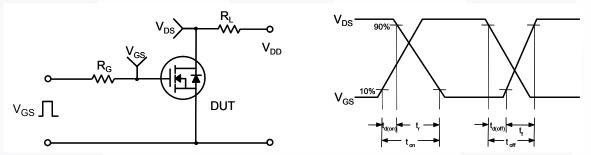


Figure 12. Resistive Switching Test Circuit & Waveforms

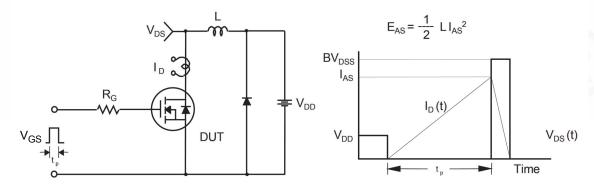


Figure 13. Unclamped Inductive Switching Test Circuit & Waveforms

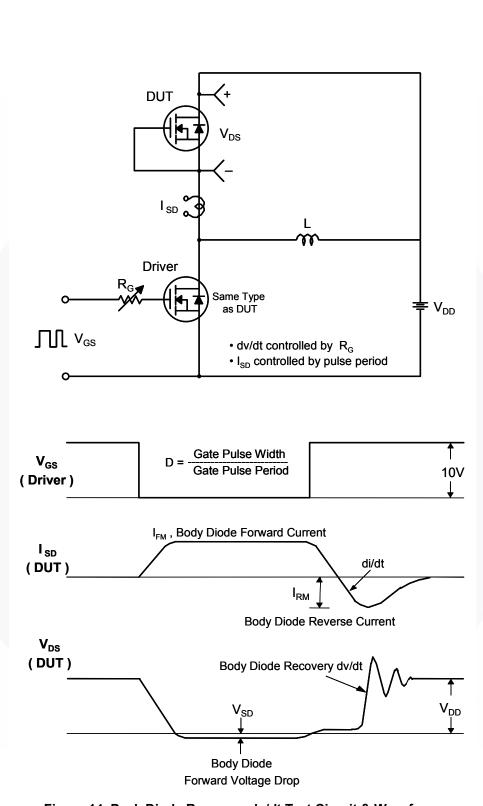


Figure 14. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

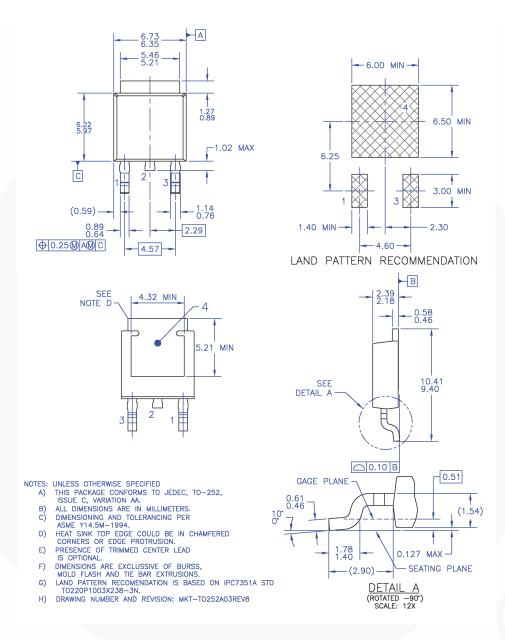


Figure 15. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

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